

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

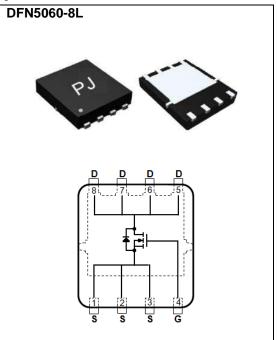
25 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@15A<34m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@10A<40m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC61249 Std.

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams
- Marking: Q5468A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	٧	
Continuous Busin Comment	T _C =25°C	1	25		
Continuous Drain Current	T _C =100°C	l _D	16	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100		
Power Dissipation	T _C =25°C	Po	48.4	14/	
	T _C =100°C		24.2	W	
Continuous Drain Current	T _A =25°C	I _D	5.5	Α	
	T _A =70°C		4.4	Α	
Power Dissipation	T _A =25°C		2.4	W	
Power Dissipation	T _A =70°C	Pb	1.6		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	24	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	3.1	°C/W	
	Junction to Ambient	R _{0JA}	62.5		

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =250uA	1.0	1.83	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =15A	-	28	34	
		V _{GS} =4.5V,I _D =10A	-	33	40	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	20	-	nC
Gate-Source Charge	Qgs	V _{DS} =30V, I _D =20A, V _{GS} =10V (Note 1,2)	-	3.8	-	
Gate-Drain Charge	Qgd	VGS=10V (Note 1,2)	-	3.9	-	
Input Capacitance	Ciss	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	1173	-	pF
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	63	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	44	-	
Turn-On Delay Time	td(on)	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	7.1	-	
Turn-On Rise Time	tr	V _{DD} =15V, I _D =1A,	-	25	-	ns
Turn-Off Delay Time	td(off)	$V_{GS}=10V, R_{G}=6\Omega$	-	31	-	
Turn-Off Fall Time	tf	(Note 1,2)	-	20	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	25	А
Diode Forward Current	I _S					
Diode Forward Voltage	V _{SD}	I _S =1A,V _{GS} =0V	-	0.72	1.2	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =22A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

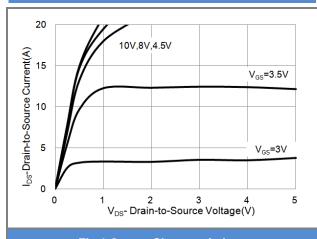
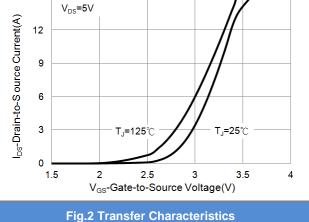


Fig.1 Output Characteristics



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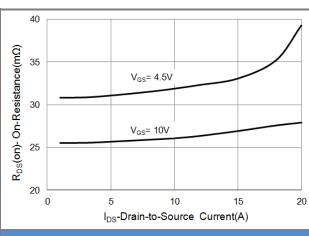


Fig.3 On-Resistance vs. Drain Current

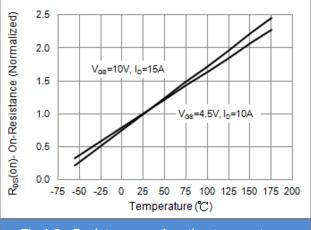


Fig.4 On-Resistance vs. Junction temperature

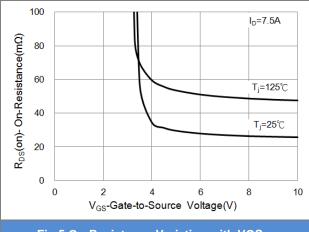


Fig.5 On-Resistance Variation with VGS.

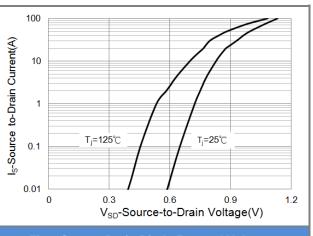


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

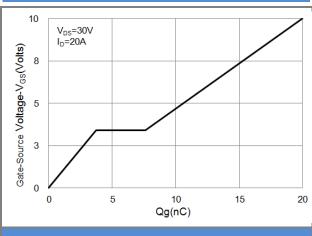


Fig.7 Gate-Charge Characteristics

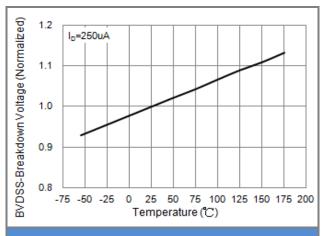


Fig.8 Breakdown Voltage Variation vs. Temperature

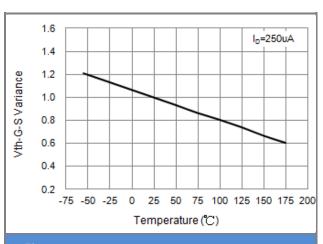


Fig.9 Threshold Voltage Variation with Temperature

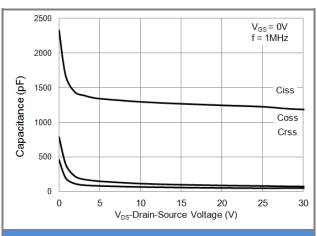
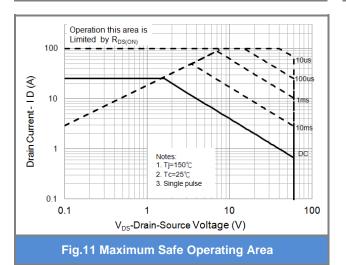


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

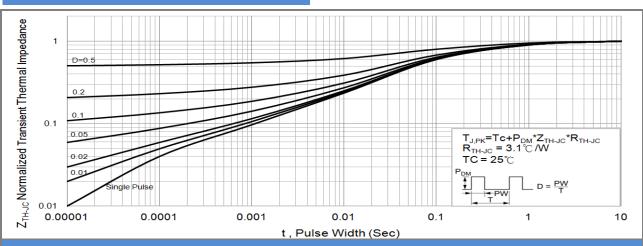


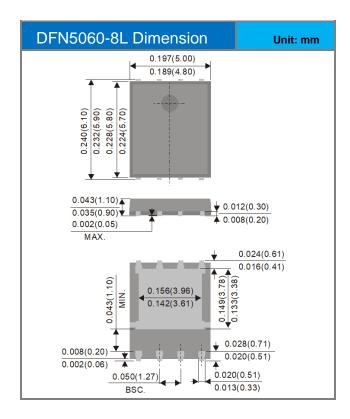
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

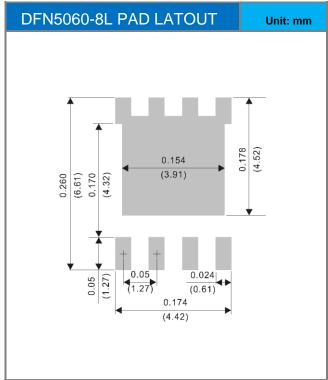


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ5468A-AU	DFN5060-8L	3000pcs / 13" reel	Q5468A	

Packaging Information & Mounting Pad Layout







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March 28,2019 PJQ5468A-AU-REV.00S Page 7